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ABOUT APPLICATION NOTE AN023

Application Note AN023 describes the methodology for designing an Akros Silicon PD/PWM component into PoE applications using a single-output flyback configuration. This document applies to all flyback designs using the AS1135, even though some diagrams may demonstrate concepts using voltages or power levels specific to only one particular design configuration.

The family of Akros AS1135 Flyback Evaluation Boards (EVB) consists of different configurations, including but not limited to the following:

- Regular PoE / local-power inputs of 36-57V
- Low local-power 12V input, plus standard 36-57V PoE input range
- 3.3V output
- 5V output
- 12V output
- Isolated synchronous
- Isolated non-synchronous
- 13W input
- 30W input

Please Refer to Application Note AN021 – AS1135-EV-Flyback Boards - User Guide for usage information on these boards.
INTRODUCTION

This guide is intended to provide general guidelines for designing with the Akros AS1135 Powered Device (PD) Controller & DC-DC Controller in flyback configuration. It is intended to be used in conjunction with the following documents:

- Akros Silicon Datasheet: AS1135 Datasheet
- Akros Silicon Application Note: AN006 – Using PoE PD with a Local Power Supply
- Akros Silicon Application Note: AN021 - AS1135 EV Flyback Board User Guide

It also provides procedures for adapting the reference designs for specific device applications.

For questions or additional information, please contact Akros Application Support engineers through your sales representative, or via email at: support@akrossilicon.com.

CIRCUIT DESIGN

PI INTERFACE

IEEE 802.3af/at-compliant systems will use either Alternative A or Alternative B power connectivity. Akros recommends that designers adhere to standard IEEE connectivity methodology.

Two external diode bridges are employed to enable connection to the Ethernet RJ45 signals, such that the PD can support any combination of Power Supply Equipment (PSE) polarity and operation mode. Note: IEEE 802.3af/at does not support that a PD be capable of operation in only one of the two modes, Alternative A or B. For compliance, designers must support all allowable combinations.

Any qualified PoE Plus (PoE+) transformer or Magjack may be used as the PI interface for 10/100/1000 or 10/100 base Ethernet system connectivity. Ferrite beads L3-L6 in Figure 13 are recommended for additional EMI filtering between the PD and the transformer center taps for robust EMI performance. Place these components close to the Ethernet transformer / Magjack. If discrete components are to be used, please consult with the Ethernet transformer vendor to ensure that it is PoE+ compatible and that input current will be well balanced between the data lines.

PD SETUP

Current Limit and Classification

RCURR and RCLASS are used for programming PD-compliance levels in the Akros AS1135 component.

RCURR sets the on-board current limit. When the pin is left unconnected, current is limited to ≤ 900mA. When connected to ground, the current limit is restricted to ≤ 500mA. Refer to the AS1135 datasheet for specific design limitations.

RCLASS sets the user-programmable classification current level. Each class represents a power-allocation range for a PD, allowing the PSE system to intelligently manage power distribution to each PD that it supports.

Recommended resistance values for the RCLASS pin are listed in Table 1. Refer to the AS1135 Datasheet for more information on resistor selection. For higher-power, pre-IEEE 802.3at applications, use of Class 4 is required.

<table>
<thead>
<tr>
<th>Class</th>
<th>Power (Watts)</th>
<th>ICLASS</th>
<th>RCLASS</th>
</tr>
</thead>
<tbody>
<tr>
<td>0</td>
<td>0.44-12.95</td>
<td>0-4 mA</td>
<td>pull-up</td>
</tr>
<tr>
<td>1</td>
<td>0.44-3.84</td>
<td>9-12 mA</td>
<td>280k Ω</td>
</tr>
<tr>
<td>2</td>
<td>3.84-6.49</td>
<td>17-20 mA</td>
<td>143k Ω</td>
</tr>
<tr>
<td>3</td>
<td>6.49-12.95</td>
<td>26-30 mA</td>
<td>90.9k Ω</td>
</tr>
<tr>
<td>4</td>
<td>Reserved</td>
<td>36-44 mA</td>
<td>63.4k Ω</td>
</tr>
</tbody>
</table>

Maintain Power Signature (MPS)

For the PD to continually receive power from the PSE, it must maintain its power signature so the PSE continues to see a valid load profile. For more info on MPS, please refer to Appendix A of Application Note AN006 – Using PoE Powered Devices with a Local Power Supply.

ISOLATED FLYBACK DC-DC CONVERTER DESIGN TECHNIQUES

The AS1135 supports isolated forward flyback and non-isolated buck DC-DC topologies. Information on the different topologies can be found in the AS1135 datasheet.

Designers must also decide whether or not their architecture requires power isolation. If the system will be non-isolated, then the high-voltage and low-voltage grounds should be connected together.

If the system will be isolated, then an opto-coupler is required on the feedback line to ensure that no DC path connects the two
sides of the circuit. To reduce common-mode noise on the Ethernet lines, a 4700pF, 2KV cap is recommended between PoE ground and board ground.

**Input Noise Filter at VDD48O**

A pi-type filter should be employed on the VDD48O pin, to reduce the amount of noise on the line. The following filter is recommended between the PD VDD48O pin and the transformer primary-winding node:

**Figure 1 - Pi-Type Filter**

![Pi-Type Filter](image1)

In addition, designers must ensure that any device connected to VDD48O be rated to safely handle at least 80V and >1A.

**Snubbing Circuit Design**

The most common snubbing circuit is the R/C, which is placed as close as practical across the device being protected. The R/C time constant of the circuit should be small in comparison to the switching period, but long relative to the voltage rise time. The capacitor must be larger than the parasitic capacitance, but as small as possible, to minimize power dissipation through the snubbing resistor.

**Figure 2 - Snubbing Circuits Used in AS1135 Flyback EVB**

![Snubbing Circuits](image2)

There are three snubbing circuits used in the AS1135 reference design shown in Figure 2. One snubbing circuit consists of R59, C35, R62, D6 and D20. Normally, resistor R62 is not installed. If R62 is to be employed, then do not place a resistor in R59. Another snubbing circuit is comprised of R78, C43, D12 and D8. The third snubbing circuit example contains C46, R90 and D16.

In designing an AS1135 snubbing circuit, designers should begin by measuring the frequency of the ring, which is placed in the snubbing circuit in place, then begin circuit tuning by adding a small capacitor (in the 100pF range) across the device and observing the ring. Then, increase the capacitance until the ring is roughly halved and note the capacitor value. The actual capacitor to be used in the design will be 75% of the capacitance value just determined.

Add a 250ohm resistor in series with this capacitor and then keep increasing the resistance until the ring is nearly eliminated. Capacitors should be the ceramic type, which have low ESR and ESL properties. Avoid wire-wound resistors, which have excessively-high ESL.

Another design consideration is the sync winding, which is used to drive the Synchronization FET. Usually a back-to-back Zener is used to clamp the winding voltage to a safe level for the \( V_{GS} = 20 \) V rating of most FETs. 0.5W, 16V Zeners are ideal for most applications.

The benefit of a Zener circuit over an R/C snubber or a gate-drive resistor is that the switching time is not affected, minimizing overlap losses. In some cases, however, a gate-drive resistor or snubber may be required. Designers should experiment to determine the optimal solution for their application.

Adding a snubbing circuit to minimize spikes and ringing can be beneficial for device protection and EMI, but the undesirable effect is a slower switching time, which impacts efficiency. Care must be taken in selecting these components and observing the effects. Board layout plays a significant role in circuit performance, along with transformer parasitics.

Besides the snubbing circuit, in the AS1135 reference designs, various EMI suppression techniques are implemented as backup solutions whenever needed. For example:

- Resistor R57 can be used to slow down the rising edge of the primary switching FET.
- Resistor R77 (not shown in Figure 2) can be added into the design between pin 11 of transformer T3 and the gate of Q4 to reduce spike stretches on the Sync FET for better EMI performance (for 5-10ohm).

Since lab test results show that Akros EVB EMI emissions are already well controlled, resistors R57 and R77 are populated with zero-ohm resistors.
Synchronization FET Selection

In general, adding a synchronization (sync) circuit, improves the DC-DC converter efficiency by a few percent. However, care must be taken when selecting the sync FET component. The major parameters important to circuit efficiency are the drain to source resistance, the rise/fall times and the total gate charge.

$R_{DS\, on}$ value should be in the 8-16 mΩ range. FET rise/fall times should be approximately 10ns. The important parameters to prevent FET component stress are the maximum drain to source voltage and the maximum gate to source voltage. Under no-load or light-load conditions, the peak voltage across the drain-to-source might exceed the $V_{DS}$ rating of the FET. System designers should tune the transformer duty cycle to minimize this stress.

One FET qualified by Akros is the International Rectifier IRF7807Z. However, IRF8714 or the ON Semiconductor NTMS4872NR2G may work as well. It is the designer’s responsibility to assure that FET and circuit parameters are not exceeded.

Akros recommended reference designs, including the recommended transformers and sync FET, have been optimized to keep node voltages around the sync FET within their desirable ranges, to avoid overstressing components.

Control-loop Stability vs. Crossover Frequency Tuning

A conventional optically-isolated error op-amp is used to compensate for control-loop stability. The system control loop shown in Figure 3 and Figure 4 has two poles, P1 and P2, and one zero, Z1, to compensate the loop.

Pole P1 is formed by AEA - the DC gain and capacitor C21. Pole P2 is created by the equivalent output capacitor and load resistor. The zero is formed from feedback compensation resistor R56 and capacitor C21.

An additional zero Z2 and pole P3 may be optionally employed for added phase margin and to cancel high-frequency noise, if required. The extra pole and zero are formed from capacitors C22 and C27 and resistor R26.
Poles and zeros are calculated with these equations:

\[ R_{LOAD} = \frac{V_{OUT}}{I_{MAX}} \]

\[ N = \frac{N_{PRIMARY}}{N_{SECONDARY}} \]

\[ D = \frac{N \cdot V_{OUT}}{(V_{IN} + N \cdot V_{OUT})} \]

\[ f_{p1} = \frac{1}{(2\pi \cdot C21)} \]

\[ f_{p2} = \frac{1}{(2\pi \cdot C_{OUT} \cdot R_{LOAD})} \]

\[ f_{z1} = \frac{1}{(2\pi \cdot C21 \cdot R56)} \]

The additional pole and zero are calculated using:

\[ f_{p3} = \frac{1}{(2\pi \cdot C27 \cdot R26)} \]

\[ f_{z2} = \frac{1}{(2\pi \cdot C22 \cdot R26)} \]

Selecting appropriate component values for pole and zero positions is the key to achieving the desired high DC gain, phase margin, gain margin and gain crossover frequency that is the hallmark of a stable system.

The general rule of thumb is to set pole P1 at the gain crossover frequency, which will determine the value for capacitor C21. The gain crossover frequency must be less than one-sixth of the switching frequency (Fsw). Then, set zero Z1 at pole P2.

The optional zero Z2 and pole P3 can be implemented if the system still requires additional phase and higher DC gain for better load regulation. When the zero associated with the output capacitor ESR (Equivalent Series Resistance) is less than one half of Fsw, this additional pole and zero can be used to compensate for or minimize the effect caused by the ESR.

Note: Once the additional pole and zero are employed in the design, zero Z2 must be set at pole P2. Zero Z1 will be set farther out at 10*P2. Set P3 equal to the zero of the ESR (Zesr), using the calculation:

\[ f_{ZESR} = \frac{1}{(2\pi \cdot C_{OUT} \cdot R_{ESR})} \]

One further issue designers should pay attention to in flyback designs is the Right Half Plan Zero (RHPZ), which can be found using the following formula:

\[ Z_{RHP} = \frac{R_{LOAD} \cdot (1 - D)^2 \cdot N^2}{(2\pi \cdot L_P \cdot D)} \]

where:

- \( R_{LOAD} \) is the load resistor
- \( D \) is the duty cycle.
- \( N \) is the turns ratio of primary to secondary
- \( L_P \) is the primary inductance of the transformer.

To minimize the effect of Right Half Plan Zero, the gain crossover frequency \( F_C \) should be also set to less than one-third of the RHPZ frequency.

Additional output filter inductor L7 may be employed, based on the design’s low output ripple and clean no/full load transient response requirements. Use of this inductor changes the impedance of the load seen by the DC-DC control loop and will require appropriate adjustments to the compensation-loop components. Also, if applications require different output capacitance than is specified in the Akros reference designs, loop compensation is affected and appropriate component tweaks will be required, using the preceding design guidelines.

Loop stability testing to generate Bode plots can be performed with a traditional small-signal test setup. Transient load-step response should also be checked, to ensure that the transient behavior matches the measured AC-loop parameters. Details for this testing, as well as selective test results on Akros reference designs, are available in Akros Application Note AN021.

Please consult with Akros’ Application Support engineers for further assistance and proper component selection.

**Opto-Coupler Biasing**

U19 is an 8-pin, optically-isolated Error-Amplifier IC containing an error amplifier and opto-coupler (see Figure 3 and Figure 4).

In order to function properly, the LED voltage at pin 8 should be greater than 2.74V and the current-transfer ratio (Ic/Itr) should be set within the minimum and maximum current-transfer ratio (CTR) over the system’s operating temperature range.

The following equations can be used to calculate the opto-coupler bias resistor values:

\[ R_{22} = \frac{(V_{OUT} - V_{LED})}{I_F} \]

\[ R_{23} = \frac{(V_{BN} - V_{COMP})}{I_C} \]
**Soft Start and Short-Circuit Protection**

The Soft Start function is enabled by grounding the CSS pin through a capacitor, as specified in the Electrical Characteristics table in the AS1135 Datasheet (Soft Ramp Time).

\[ R64 = \left( \frac{V_{OUT} - V_{REF}}{I_{SCOMP}} \right) \]

- \( I_C/I_F \) is the current transfer ratio
- \( I_F \) is the LED current set by R22
- \( I_C \) is the collector current set by R23
- \( I_{SCOMP} \) is the current flow into the error amplifier compensation pin 6 of U19.
- Akros-recommended voltage levels: \( V_{LED} = 2.74V, V_{COMP} = 1.8V, V_{REF} = 1.24V \).

In general, LED current \( I_F \) is set between 2mA and 3mA, to reduce power dissipation and extend the life of the opto-coupler. R64 is used to supply 1-2mA into the error amplifier, to minimize CTR variation over the entire temperature range.

**Figure 5 - Short-Circuit Protection**

Short-circuit protection for the device may be added to limit PD input current or shut down the IC if a short occurs in the application hardware. As shown in Figure 5, the optional short-circuit protection schematic consists of the following components: C18, D18, Q5, R28, R83, and R84.

The potential difference between bias winding pin 5 and 6 of power transformer T3 is about 6.5V when the EVB is operating steady state. Resistor R28 is selected small enough to ensure that the voltage at the base of transistor Q5 is biased at more than 3.5V. Capacitor C18 is used to hold up the charge, so that the base voltage of the transistor is higher than its emitter voltage, which is the voltage at the AS1135’s COMP pin minus one diode voltage drop. Transistor Q5 stays biased ‘off’ during normal steady state operation, keeping the short protection circuit inactive.

However, if the output load becomes shorted, the output voltage will lose regulation. The IC is forced to run at minimum duty cycle in flyback topology. As a result, the base voltage of Q5 will drop below 0.7V, due to the dropping bias-winding voltage when the DC-DC converter output is shorted. Therefore, Q5 is turned on and pulls the AS1135 COMP pin voltage down close to ground. This limits the input current to less than 100mA until the short is removed.

**LV Mode Network vs. Input Voltage**

There are still a number of applications that require local power delivery for redundancy or when Ethernet connections at the site are not PoE-capable.

By providing for the use of a wall power adapter, users have the ability to deploy the same equipment in both PoE and non-PoE environments. This also provides a ready migration path when PoE is installed later on.

Diode D13 (see Figure 13 on page 18) is used to block a reversing current from VDD480. Its maximum leakage current should be specified to be less than 350µA. Local power cabling can cause EMI problems, so appropriate choke/filtering components should be used to isolate the local power jack.

Refer to the AS1135 Datasheet and Application Note AN006 – Using PoE Powered Devices with a Local Power Supply for proper local-voltage mode network setup.

**Power Transformer Selection**

For the regular PoE input voltage, the transformer selection can be relatively easy and the recommended vendors can provide the support needed in the most cases. However, if the local source voltage is significantly lower than the PoE line (<32V), then special consideration must be taken in the transformer circuit design.

Refer to AN006 – Using PoE Powered Devices with a Local Power Supply for a list of qualified power transformers used in different configurations.
Akros has a selection of recommended transformers from leading magnetic suppliers that have been tested for proper circuit performance. Akros highly recommends adhering to Akros-proven transformer designs for optimal system cost and performance, and to minimize the need for design re-optimization and validation.

**COMPONENT PLACEMENT**

Component selection and layout placement is very important for good EMI, efficiency and output ripple performance. Appendix A provides example evaluation board schematics for a power splitter design with an isolated flyback DC-DC converter. Example layouts from this board are also provided, to illustrate desirable design and layout practices.

**ETHERNET SIGNALS**

No special placement consideration is required for the Ethernet line components when designing with the AS1135; however, the PD device should be placed as close to the center tap of the transformer as possible, to limit the IR drop.

**DC-DC CONVERTER**

When using flyback topology, the NDRV FET and its associated protection diodes should be placed as close as practical to the PD/PWM Controller component. Ideally, place them on the reverse side of the board, underneath the PD/PWM Controller. The DC-DC transformer should be placed on the top side of the board, to limit the distance between the switching FETs and the transformer.

Ceramic bypass capacitor C10 should be placed as close as possible to the PD/PWM Controller for optimum sourcing of the switching current from the gate drive of the power FET. This will assist in minimizing high-frequency ringing and ripple at the VBN pin of the AS1135 component. The same applies for decoupling capacitors C1 and C11.

Snubber circuits should be placed very close to the primary or secondary FET where snubbing is required. They may be placed on the back side of the FETs, as appropriate.

When placing components on both sides of the PCB, thermal issues should be carefully considered. All active components in the design (AS1135, FETs, diodes, etc.) require careful layout and ground plane connectivity for thermal management. To minimize the board’s thermal density and localized heating, no two active components should be placed back-to-back on opposite sides of the board.

The placement of the 2KV capacitors C13 and C14 is critical for proper EMI performance. It is recommended that one be placed on each side of transformer T3, to allow for design flexibility during testing.
COMPONENT PLACEMENT EXAMPLE

Figure 6 and Figure 7 show example component placements for the top and bottom of a PC board:

Figure 6 - Top-Side Component Placement
Figure 7 - Bottom-Side Component Placement
**ROUTEING**

**ETHERNET SIGNALS**

Ethernet signal routing on the secondary side of the input transformer should follow the recommendations of the Ethernet PHY supplier. The AS1135 does not require additional consideration.

In general, Ethernet data signals are high-frequency differential signaling channels. Their routing should have 100ohm differential impedance on both sides of the inputs to the Ethernet transformer. Signal traces should avoid sharp bends and sudden width changes, since this affects impedance and current carrying capacity. Traces should also have appropriate ground planes underneath, for common-mode signal return and to shield against coupled noise from the DC-DC converter.

High-speed signals should be routed away from the DC-DC converter, to prevent the converter switching noise from appearing on the data lines.

Since the Ethernet transformer center-tap connections do not carry data traffic, these traces should be drawn wider on the circuit board to minimize the IR drop due to the relatively large current (up to 1A) to and from the line. The increased width is also recommended in order to carry this current without excessive heating.

Ground planes should be solid and free of islands and choke points, to ensure a low-impedance return path.

**DC-DC CONVERTER**

VDD48O signal routing should be at least 200mils wide and all components directly connected to it should also be 200mils, including the routing to the drain and gate of the FET between the NDRV and the primary side of the transformer.

Traces leading from the secondary side of the DC-DC converter should be appropriate for the output current of the converter. For maximum power delivery, it is also recommended that a minimum 200mil line width be used. Any layer transitions for these high-power signals require multiple vias to ensure low inductance and resistance. The length of all high-impedance small signal traces should be kept to a minimum and shielded from the switching power traces.

The AS1135’s PADDLE should be tied directly to the return of C7 and C8, in a path that will not share the high-power current associated with the DC-DC converter.

Minimizing the loop area for all high-frequency switching currents helps reduce radiated EMI. Ceramic capacitors C7 and C8 supply the high-frequency switching current for the primary side of the integrated converter block in the PD Controller. The loop area made by C7 and C8 with the return path tying to the current-sense resistor R11 should be minimized.

**THERMAL PAD**

The Akros-recommended 5x5mm 20-LD QFN footprint for the AS1135 package should be followed. It is essential that the bottom-side pad be used for both thermal and electrical contact. A good solder connection is essential for optimal performance. This pad should be filled with as many vias as is practical, to ensure good thermal conductivity to the board’s ground plane.

It is also recommended that a metal pad be placed on the bottom side of the board. Avoid routing signals underneath. A minimum of nine vias on the ground/thermal pad is required. For additional information, refer to Application Note AN018 – Thermal Characterization & QFN Layout Guide and AN022 – AS1135 Thermal Characterization Report.

**STACK-UP AND GENERAL LAYOUT GUIDELINES**

For a multilayer board, ground and signal layers should be internal layers, with 1oz copper pour on both the top and bottom layers. Stitch the copper pour areas with ground layers of no greater than 7mm pitch, to avoid islands. This will help with thermal conduction, EMI emission and immunity. Separate active signal layers, both to ensure good capacitance between the layers and to ensure there is a solid reference or return for the active signals.

**GROUND LAYERS**

The DC-DC converter creates voltages isolated from the high-voltage signals coming in from the Ethernet line. For this reason, two grounds are designed into the system, one for high voltage and one for low voltage.

Grounds should be separated by a gap on the power and ground planes, to reduce DC-DC noise coupling to the Ethernet signals. Akros recommends a minimum gap of 50mils. Ground planes should be 1oz copper and should be as continuous as possible, with no isolated islands or narrow choke points.

To maintain ground separation, secondary-side components and routing should be placed over the low-voltage ground plane. Primary-side components and routing should be placed over the high-voltage ground plane.

Maintain sufficient spacing between the traces leading to the power transformer, as well as between the traces from the transformer to other components on the board, to avoid isolation-related issues.

For EMI consideration, Akros recommends not filling in the ground plane under the power transformer, as shown in the layout example. This reduces the coupling of switching events from the magnetic transformer to the ground plane. The high voltage/PoE ground should be treated as an island covered by the low-voltage ground, as shown in Figure 10. Via stitching should be used on the outer edges of the board, to ensure low-impedance connectivity between the layers.
LAYOUT EXAMPLE

Figure 8 to Figure 12 are example layouts that apply to the AS1135. Appendix A has corresponding schematics for the implementation of a synchronized flyback-isolated converter.

Note that these designs include footprints and place holders for a wide range of components, to allow Akros to modify the design to meet various power, voltage and feature requirements. An application-specific design may be somewhat simplified based on the designer’s specific requirements.

Figure 8 - Layout Example – Top Assembly
Figure 9 - Layout Example – Top Layer
Figure 10 - Recommended Ground Plane Split using Magjack – Shown in Ground Layers 1, 2 and 3
Figure 12 - Layout Example – Bottom Assembly
APPENDIX A - EXAMPLE SCHEMATICS

Figure 13 - Schematic of AS1135-EV-SYNC-FL5V30W (Line Interface and PD)
Figure 14 - Schematic of AS1135-EV-SYNC-FL5V30W (DC-DC Converter)
REFERENCE MATERIALS

- Akros Silicon Datasheet: AS1135 Datasheet
- Akros Silicon Application Note: AN006 – Using PoE PD with a Local Power Supply
- Akros Silicon Application Note: AN021 - AS1135 EV Flyback Board User Guide
- Evaluation Boards (containing reference designs):
  - AS1135-EV-FL3.3-30W
  - AS1135-EV-FL5-30W
  - AS1135-EV-FL3.3-30W
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